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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Serial Number: 10/646,478 Filing Date: August 22, 2003

Title: STACKED VIA STRUCTURE THAT INCLUDES A SKIP VIA

Assignee: Intel Corporation

IN THE CLAIMS

The pending claims are reproduced herein for the Examiner's convenience.

1-39. (Canceled)

- 40. (Previously Presented) A substrate comprising:
- a first dielectric layer;
- a second dielectric layer;
- a first conductive layer between the first and second dielectric layers;
- a third dielectric layer, the second dielectric layer being between the first and third dielectric layers;
- a second conductive layer between the second dielectric layer and the third dielectric layer, the second conductive layer including a first skip via that extends through the first and second dielectric layers; and
- a third conductive layer on the third dielectric layer, the third conductive layer including a second via that extends through the third dielectric layer, the second via and the first skip via being stacked on top of one another.
- 41. (Previously Presented) The substrate of claim 40 wherein the first skip via includes a longitudinal axis and the second via includes a longitudinal axis, the longitudinal axis of the first skip via being substantially aligned with the longitudinal axis of the second via.
- 42. (Previously Presented) The substrate of claim 41 wherein the first, second and third dielectric layers are formed on a core.
- 43. (Previously Presented) The substrate of claim 42 further comprising a fourth conductive layer between the first dielectric layer and the core.

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44. (Previously Presented) The substrate of claim 40 wherein the first, second and third conductive layers are patterned conductive layers.

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- 45. (Previously Presented) The substrate of claim 40 wherein the first skip via has a diameter between 49um and 85um and the second via has a diameter between 49um and 85um.
- 46. (Previously Presented) The substrate of claim 40 wherein the first skip via has a length between 58um and 92um and the second via has a length between 24um and 36um.
 - 47. (Previously Presented) A substrate comprising:
 - a first dielectric layer;
 - a second dielectric layer;
 - a first conductive layer between the first and second dielectric layers;
- a third dielectric layer, the second dielectric layer being between the first and third dielectric layers;
- a second conductive layer between the second and third dielectric layers, the second conductive layer including a first skip via that extends through the first and second dielectric layers;
- a fourth dielectric layer, the third dielectric layer being between the second and fourth dielectric layers;
 - a third conductive layer between the third and fourth dielectric layers; and
- a fourth conductive layer on the fourth dielectric layer, the fourth conductive layer including a second skip via that extends through the third and fourth dielectric layers, the second skip via and the first skip via being stacked on top of one another.
- 48. (Previously Presented) The substrate of claim 47 wherein the first skip via and the second skip via each include a longitudinal axis, the longitudinal axis of the first skip via being substantially aligned with the longitudinal axis of the second skip via.

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49. (Previously Presented) The substrate of claim 47 wherein the first, second, third and fourth dielectric layers are formed on a core.

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- 50. (Previously Presented) The substrate of claim 49 further comprising a fifth conductive layer between the first dielectric layer and the core.
- 51. (Previously Presented) The substrate of claim 47 wherein the first, second, third and fourth conductive layers are patterned conductive layers.
- 52. (Previously Presented) The substrate of claim 47 wherein the first skip via has a diameter between 49um and 85um and the second skip via has a diameter between 49um and 85um.
- 53. (Previously Presented) The substrate of claim 47 wherein the first skip via has a length between 58um and 92um and the second skip via has a length between 58um and 92um.
 - 54. (Previously Presented) The substrate of claim 47 further comprising:
- a fifth dielectric layer, the fourth conductive layer being between the fourth and fifth dielectric layers;
- a sixth dielectric layer, the fifth dielectric layer being between the fourth and sixth dielectric layers;
 - a fifth conductive layer between the fifth and sixth dielectric layers;
- a sixth conductive layer on the sixth dielectric layer, the sixth conductive layer including a third skip via that extends through the fifth and sixth dielectric layers.
- 55. (Previously Presented) The substrate of claim 54 wherein the first, second and third skip vias each include a longitudinal axis, the longitudinal axis of the first skip via being substantially aligned with the longitudinal axis of the second and third skip vias.

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56. (Previously Presented) The substrate of claim 54 wherein the first, second, third, fourth, fifth and sixth conductive layers are patterned conductive layers.

- 57. (Previously Presented) The substrate of claim 54 wherein the first, second and third skip via each have a diameter between 49um and 85um.
- 58. (Previously Presented) The substrate of claim 54 wherein the first, second and third skip via each have a length between 58um and 92um.

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